

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Hiroshi Tayanaka ATTORNEY DOCKET NO. P97,0027 01  
SERIAL NO. GROUP ART UNIT: 2813  
FILING DATE: EXAMINER: K. Christiansen  
INVENTION: "THIN FILM SEMICONDUCTOR AND METHOD FOR MAKING  
THIN FILM SEMICONDUCTOR" —



which is a Continuation Application of the following U.S. Application

APPLICANT: Hiroshi Tayanaka ATTORNEY DOCKET NO. P97,0027 —  
SERIAL NO. 08/818,239 GROUP ART UNIT: 2813  
FILING DATE: March 14, 1997 EXAMINER: K. Christiansen  
INVENTION: "METHOD FOR MAKING THIN FILM SEMICONDUCTOR (AS  
AMENDED)"

INFORMATION DISCLOSURE STATEMENT

Hon. Assistant Commissioner of Patents  
Washington, D.C. 20231

S I R:

I. INTRODUCTION

In accordance with the provisions of 37 C.F.R. Section 1.56, applicant requests that citation and examination of the documents identified on the attached form PTO 1449 be made during the course of the prosecution of the above-identified patent application.

II. DOCUMENTS

	<u>U.S. PATENT DOCUMENT</u>	<u>PATENTEE</u>	<u>ISSUED</u>
✓ AA	5,362,683	T. Takenaka, et al.	11-08-94
✓ AB	4,727,047	C. Bozler, et al.	02-23-88
✓ AC	5,811,348	T. Matsushita, et al.	09-22-98
✓ CAD	5,854,123	N. Sato, et al.	12-29-98
✓ AE	5,856,229	K. Sakaguchi, et al.	01-05-99

✓ *Continuation* 6/29/2001

09/016395

	<u>FOREIGN PATENT DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>PUBLICATION DATE</u>
AL <sup>xc</sup>	EP 0 554 795	Europe	08-11-93
AM <sup>xc</sup>	EP 0 793 263	Europe	09-03-97
AN <sup>x</sup>	JP62-279625	Japan	12-04-87

OTHER ITEMS OF INFORMATION

AT<sup>xc</sup> Patent Abstracts of Japan, Vol. 10, No. 039 (E-381), February 15, 1986 & JP60-196955 (Toko, Inc.), October 5, 1985

AU<sup>xc</sup> Patent Abstracts of Japan, Vol. 18, No. 066 (E-1501), February 3, 1994 & JP05-283722 (Canon, Inc.), October 29, 1993

AV<sup>xc</sup> T. Yasumatsu, et al., "Ultrathin Si films grown epitaxially on porous silicon", Applied Surface Science, Vol. 48/49, May 1991, pp. 414-418, XP002093161

AW<sup>xc</sup> M. Ohnishi, et al., "New Type Structures of A-Si Solar Cell Submodules Fabricated by Microscopic Hole Spacing Technique", Record of the Photovoltaic Specialists Conference, Kissimmee, May 21-25, 1990, Vol. 2, No. Conf. 21, May 21, 1990, pp. 1394-1399, XP000480389, Institute of Electrical and Electronics Engineers

AX<sup>xc</sup> V. Labunov, et al., "Heat Treatment Effect on Porous Silicon", Thin Solid Films, Vol. 137, pp. 123-134, 1986

AY<sup>xc</sup> N. Sato, et al., "Epitaxial Growth on Porous Si for a New Bond and Etch-back SOI", The Electrochemical Society, Spring Meeting, May 22-27, 1994, Extended Abstracts, Vol. 94-1, Abstract No. 443, pp. 705-706

AZ<sup>x</sup> "Crystalline Silicon and Doping", Maruzen Kabushiki Kaisha Publisher, 1986

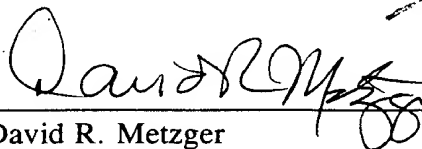
III. REMARKS

*X. Chien* 7/2/2001  
6/27/2002

The above items of information, AA-AE, AL-AN and AT-AZ, were made of record in the parent of this continuation application, U.S. application Serial No. 08/818,239 filed

March 14, 1997, and its parent application Serial No. 08/595,382 filed February 1, 1996.  
Therefore, copies of these references are not separately provided herewith

Respectfully submitted,

A handwritten signature in black ink, appearing to read "David R. Metzger", with a large, stylized initial "D" and "M".

, Reg. 32,919

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